ON Semiconductor

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790DF

Generic Copy

Issue Date: 24-Jun-2014

TITLE: Final PCN for wafer fab transfer from Gifu to the wafer fab United Microelectronics Corporation Taiwan (UMCT). (Group DF)

PROPOSED FIRST SHIP DATE: starting on 24 Sep 2014 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com

SAMPLES: Contact your local ON Semiconductor Sales Office or Shigehito.Matsumoto@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available
Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:
Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the transfer of products from Sanyo wafer fabrication sites located in Gifu to the wafer fabrication United Microelectronics Corporation Taiwan (UMCT).

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

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RELIABILITY DATA SUMMARY

Group DF Except EFC6601R-TR

Test:	Conditions:	Interval:	Results
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC,VDSS=max	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03×10^{5}Pa,100%	50 hrs	Pass
Resistance to Soldering heat(Reflow)	Solder Temp.:260degC±5degC	10s	Pass
Solderability	Solder Temp.: 245degC±5degC	5s	Pass

Group DF Only for EFC6601R-TR

Test:	Conditions:	Interval:	Results
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC,VDSS=max	1000 hrs	Pass
Temperature Cycle	Ta=-40degC to 125degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=110degC,1.2×10^{5}Pa, 85%	50 hrs	Pass
Resistance to Soldering heat(Reflow)	Solder Temp.:260degC±5degC	10s	Pass
Solderability	Solder Temp.: 245degC±5degC	5s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY

No change to the device data sheets is being made. All parametric performance and limits remain the same.

CHANGED PART IDENTIFICATION

No change to current part making will occur. Making traceability codes will be able to identify wafer fab die source.

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List of affected parts:

Group DF

PART_ID
ATP103-TL-H
ATP106-TL-H
ATP114-TL-H
ATP301-TL-H
CPH6341-TL-E
ECH8310-TL-H
ECH8601M-C-TL-H
ECH8601M-C-TL-HX
ECH8651R-R-TL-HX
ECH8651R-TL-HX
ECH8661-TL-H
ECH8663R-TL-H
EFC6601R-TR